HALOGEN

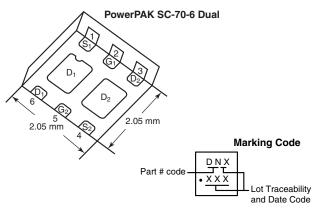
FREE



Vishay Siliconix

Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I _D (A)	Q _g (Typ.)		
- 30	0.064 at V _{GS} = - 10 V	- 4.5 ^a			
	0.078 at $V_{GS} = -4.5 \text{ V}$	- 4.5 ^a	6.6 nC		
	0.120 at V _{GS} = - 2.5 V	- 4.5 ^a			



Ordering Information:

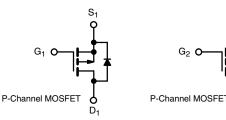
SiA929DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Gen III Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- 100 % R_a Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Load Switch and Battery Management for Smart Phones, Tablet PCs and Portable Media Players
- Fast Battery Charging



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	- 30	V	
Gate-Source Voltage		V_{GS}	± 12	 	
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	I _D	- 4.5 ^a - 4.5 ^a - 4.3 ^{b, c} - 3.4 ^{b, c}	A	
Pulsed Drain Current (t = 300 μs)		I _{DM}	- 15		
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C$	I _S	- 4.5 ^a - 1.6 ^{b, c}		
Maximum Power Dissipation	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	P _D	7.8 5 1.9 ^{b, c} 1.2 ^{b, c}	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}		Ü	260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	52	65	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	12.5	16		

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See Solder Profile (www.vishav.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 110 °C/W.

Document Number: 63398 S11-1654-Rev. A, 15-Aug-11

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$ $\Delta V_{GS(th)}/T_{J}$			- 23		mV/°C	
V _{GS(th)} Temperature Coefficient		I _D = - 250 μA		1.5			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.6		- 1.1	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
7 0 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 10			Α	
		V _{GS} = - 10 V, I _D = - 3 A		0.052	0.064	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 2 A		0.062	0.078		
	, ,	V _{GS} = - 2.5 V, I _D = - 1 A		0.090	0.120		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 3 A		10		S	
Dynamic ^b							
Input Capacitance	C _{iss}			575		pF	
Output Capacitance	C _{oss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		60			
Reverse Transfer Capacitance	C _{rss}			51			
·	Q _g	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 4.3 A		14	21	nC	
Total Gate Charge				6.6	10		
Gate-Source Charge		$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.3 \text{ A}$		1.2			
Gate-Drain Charge	Q_{gd}			1.9			
Gate Resistance	R_g	f = 1 MHz	1.1	5.5	11	Ω	
Turn-On Delay Time	t _{d(on)}			15	30		
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_{L} = 4.4 \Omega$		18	35		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 3.4 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		22	40		
Fall Time	t _f			10	20		
Turn-On Delay Time	t _{d(on)}			5	10	ns	
Rise Time	t _r	V_{DD} = - 15 V, R_{L} = 4.4 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 3.4 A, V_{GEN} = - 10 V, R_g = 1 Ω		22	40		
Fall Time	t _f			10	20		
Drain-Source Body Diode Characteristi	cs			1	'	•	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.5	Δ	
rulse Diode Forward Current I _{SM}					- 15	A	
Body Diode Voltage	V_{SD}	I _S = - 3.4 A, V _{GS} = 0 V		- 0.89	- 1.2	V	
Body Diode Reverse Recovery Time t _{rr}				20	40	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = - 3.4 A, dl/dt = 100 A/μs, T _J = 25 °C		10	20	nC	
Reverse Recovery Fall Time	t _a	$_{1F} = -3.4 \text{ A}, \text{ u/u} = 100 \text{ A/}\mu\text{s}, \text{ I}_{J} = 25 \text{ C}$		9		ns	
Reverse Recovery Rise Time	t _b			11			

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

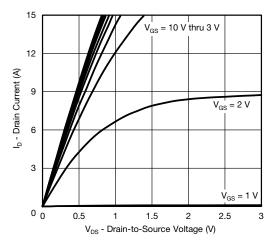
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

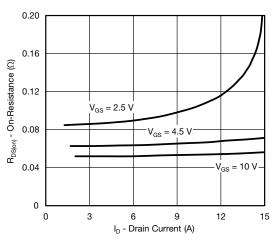


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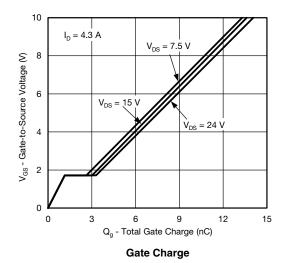
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

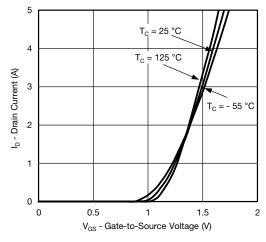


Output Characteristics

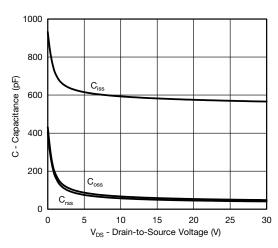


On-Resistance vs. Drain Current and Gate Voltage

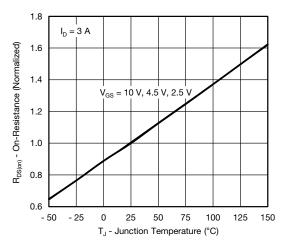




Transfer Characteristics



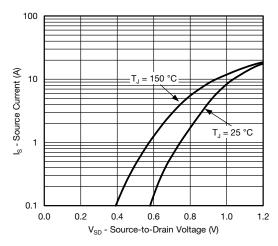
Capacitance



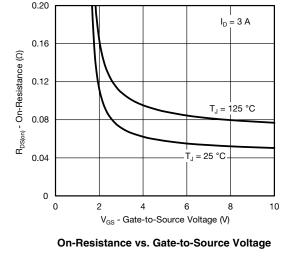
On-Resistance vs. Junction Temperature

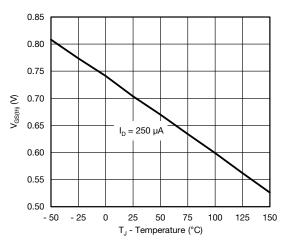
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

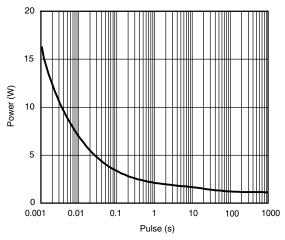


Soure-Drain Diode Forward Voltage

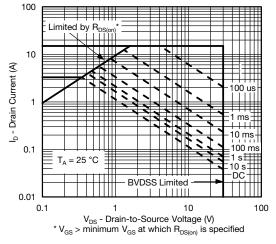




Threshold Voltage



Single Pulse Power, Junction-to-Ambient

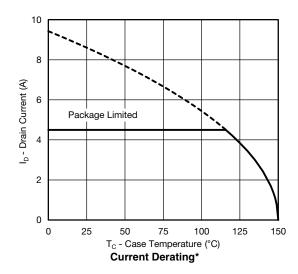


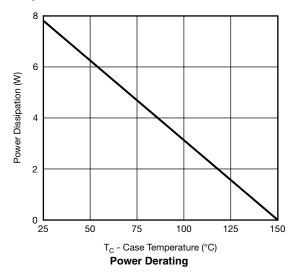
Safe Operating Area, Junction-to-Ambient



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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



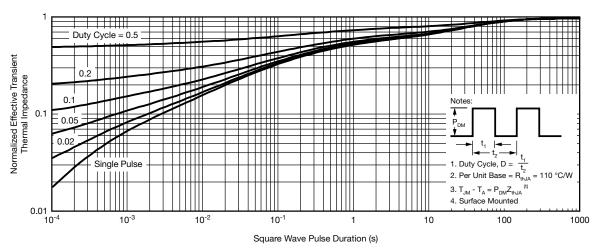


 $^{^*}$ The power dissipation P_D is based on $T_{J(max)}$ = 150 $^{\circ}$ C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

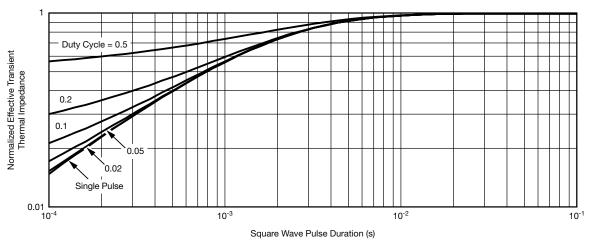
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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Revision: 11-Mar-11



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